

## MOS FIELD EFFECT TRANSISTOR

# $\mu$ PA502T

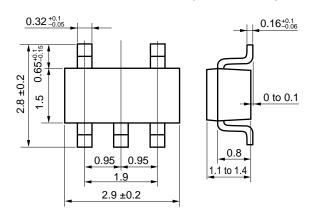
#### N-CHANNEL MOS FET (5-PIN 2 CIRCUITS)

The  $\mu$ PA502T is a mini-mold device provided with two MOS FET circuits. It achieves high-density mounting and saves mounting costs.

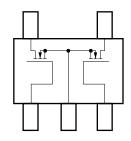
#### **FEATURES**

- Two source common MOS FET circuits in package the same size as SC-59
- Complement to μPA503T
- · Automatic mounting supported

#### PACKAGE DIMENSIONS (in millimeters)



#### PIN CONNECTION (Top view)



#### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

| PARAMETER               | SYMBOL                  | RATINGS     | UNIT |  |
|-------------------------|-------------------------|-------------|------|--|
| Drain to Source Voltage | VDSS                    | 50          | V    |  |
| Gate to Source Voltage  | Vgss                    | ±20         | V    |  |
| Drain Current (DC)      | I <sub>D(DC)</sub>      | 100         | mA   |  |
| Drain Current (pulse)   | I <sub>D(pulse)</sub> * | 200         | mA   |  |
| Total Power Dissipation | Рт                      | 300 (TOTAL) | mW   |  |
| Channel Temperature     | Tch                     | 150         | °C   |  |
| Storage Temperature     | Tstg                    | -55 to 150  | °C   |  |

<sup>\*</sup> PW  $\leq$  10 ms, Duty Cycle  $\leq$  50 %

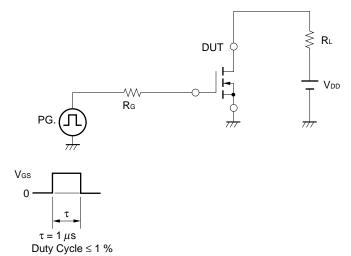


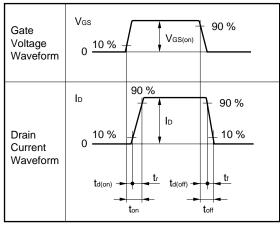
### ELECTRICAL CHARACTERISTICS (TA = 25 °C)

| PARAMETER                           | SYMBOL               | TEST CONDITIONS N                                              |     | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|----------------------------------------------------------------|-----|------|------|------|
| Drain Cut-off Current               | IDSS                 | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0                    |     |      | 1.0  | μΑ   |
| Gate Leakage Current                | Igss                 | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$                        |     |      | ±1.0 | μΑ   |
| Gate Cut-off Voltage                | VGS(off)             | $V_{DS} = 5.0 \text{ V}, I_{D} = 1.0 \mu A$                    | 0.8 | 1.4  | 1.8  | V    |
| Forward Transfer Admittance         | yfs                  | V <sub>DS</sub> = 5.0 V, I <sub>D</sub> = 10 mA                | 20  |      |      | mS   |
| Drain to Source On-State Resistance | RDS(on)1             | Vgs = 4.0 V, ID = 10 mA                                        |     | 19   | 30   | Ω    |
| Drain to Source On-State Resistance | R <sub>DS(on)2</sub> | Vgs = 10 V, ID = 10 mA                                         |     | 15   | 25   | Ω    |
| Input Capacitance                   | Ciss                 | V <sub>DS</sub> = 5.0 V, V <sub>GS</sub> = 0, f = 1.0 MHz      |     | 16   |      | pF   |
| Output Capacitance                  | Coss                 |                                                                |     | 12   |      | PF   |
| Reverse Transfer Capacitance        | Crss                 |                                                                |     | 3    |      | pF   |
| Turn-On Delay Time                  |                      | $t_{d(on)} V_{GS(on)} = 5.0 \text{ V}, \text{ Rg} = 10 \Omega$ |     | 17   |      | ns   |
| Rise Time                           | tr                   | V <sub>DD</sub> = 5.0 V, I <sub>D</sub> = 10 mA                |     | 10   |      | ns   |
| Turn-Off Delay Time                 | td(off)              | $R_L = 500 \Omega$                                             |     | 68   |      | ns   |
| Fall Time                           | <b>t</b> f           |                                                                |     | 38   |      | ns   |

Marking: DA

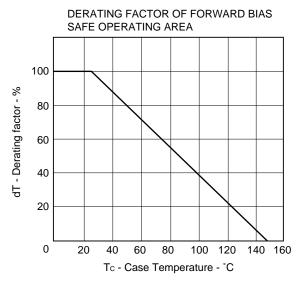
## SWITCHING TIME MEASUREMENT CIRCUIT AND MEASUREMENT CONDITIONS (RESISTANCE LOADED)

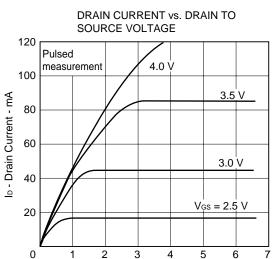




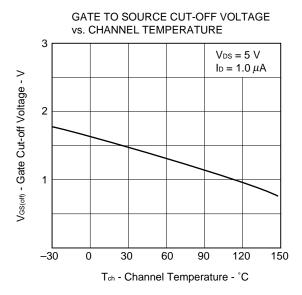


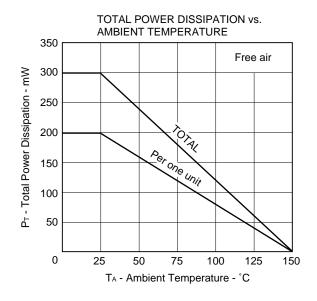
#### TYPICAL CHARACTERISTICS (TA = 25 °C)

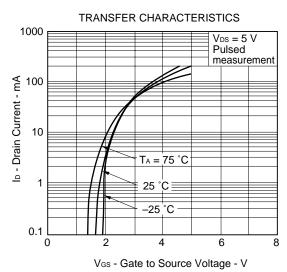


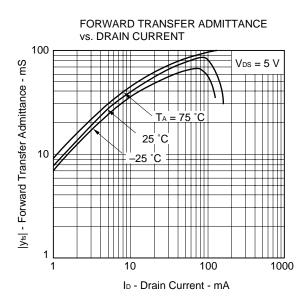


V<sub>DS</sub> - Drain to Source Voltage - V



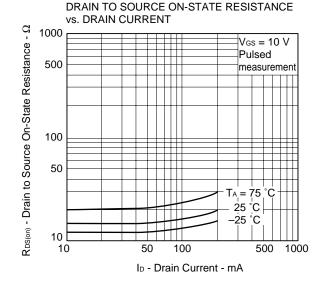


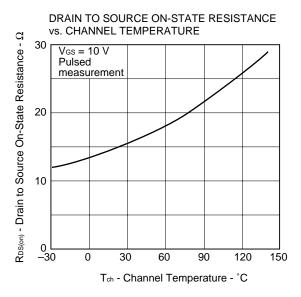




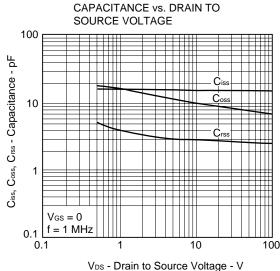
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE $\mathsf{R}^{\mbox{\tiny DS}(\mbox{\tiny On})}$ - Drain to Source On-State Resistance - $\Omega$ 100 I<sub>D</sub> = 10 mA Pulsed 50 measurement 10 5

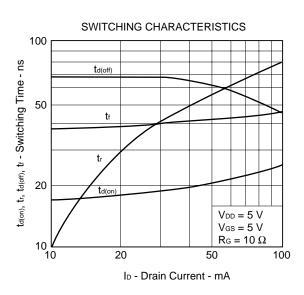
100

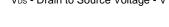


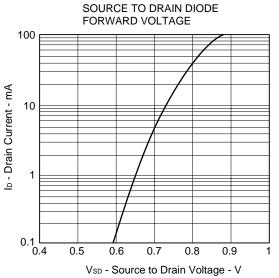


V<sub>GS</sub> - Gate to Source Voltage - V











#### **REFERENCE**

| Document Name                                               | Document No. |  |
|-------------------------------------------------------------|--------------|--|
| NEC semiconductor device reliability/quality control system | TEI-1202     |  |
| Quality grade on NEC semiconductor devices                  | IEI-1209     |  |
| Semiconductor device mounting technology manual             | C10535E      |  |
| Guide to quality assurance for semiconductor devices        | MEI-1202     |  |
| Semiconductor selection guide                               | X10679E      |  |



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Anti-radioactive design is not implemented in this product.

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